

DESCRIPTION

The 3401 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

GENERAL FEATURES

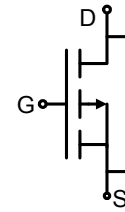
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V_{DSS}	$R_{DS(ON)}$ @ 10V (Typ)	$R_{DS(ON)}$ @ 4.5V (Typ)	$R_{DS(ON)}$ @ 2.5V (Typ)	I_D
-30V	46m Ω	55m Ω	74m Ω	-4.2A

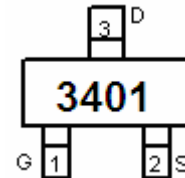
- High Power and current handling capability
- RoHS Compliant
- Surface Mount Package

Application

- PWM applications
- Load switch
- Power management



Schematic diagram



Marking and pin Assignment



SOT-23

Ordering Information

Part Number	Marking	Case	Packaging
3401	3401	SOT-23	3000pcs/Reel

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	-4.2	A
Drain Current-Pulsed (Note 1)	I_{DM}	-30	A
Maximum Power Dissipation	P_D	1.2	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	104	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-24V, V_{GS}=0V$	-	-	-1	μA

Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-0.7	-1	-1.3	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-4.2A	-	46	65	mΩ
		V _{GS} =-4.5V, I _D =-4A	-	55	75	mΩ
		V _{GS} =-2.5V, I _D =-1A		74	129	mΩ
Forward Transconductance	g _{FS}	V _{DS} =-5V,I _D =-4.2A	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =-15V,V _{GS} =0V, F=1.0MHz	-	950	-	PF
Output Capacitance	C _{oss}		-	115	-	PF
Reverse Transfer Capacitance	C _{rss}		-	75	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =-15V,I _D =-3.2A V _{GS} =-10V,R _{GEN} =6Ω	-	7	-	nS
Turn-on Rise Time	t _r		-	3	-	nS
Turn-Off Delay Time	t _{d(off)}		-	30	-	nS
Turn-Off Fall Time	t _f		-	12	-	nS
Total Gate Charge	Q _g	V _{DS} =-15V,I _D =-4A,V _{GS} =-4.5V	-	9.5	-	nC
Gate-Source Charge	Q _{gs}		-	2	-	nC
Gate-Drain Charge	Q _{gd}		-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-1A	-	-	-1	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

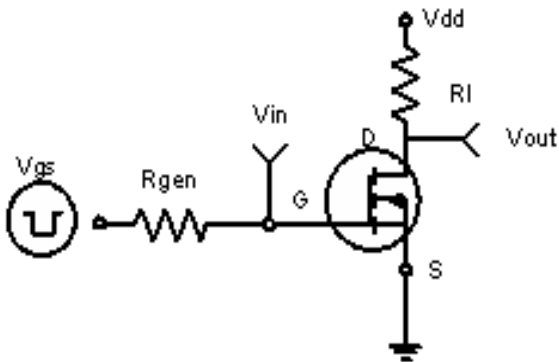


Figure 1: Switching Test Circuit

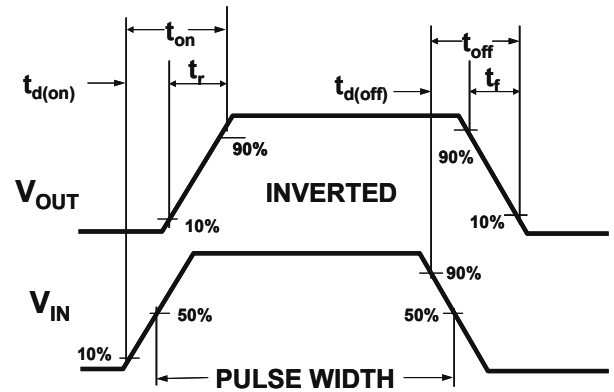


Figure 2: Switching Waveforms

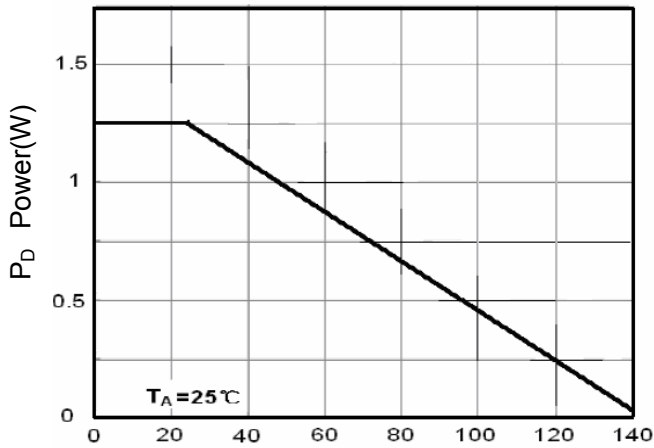


Figure 3 Power Dissipation

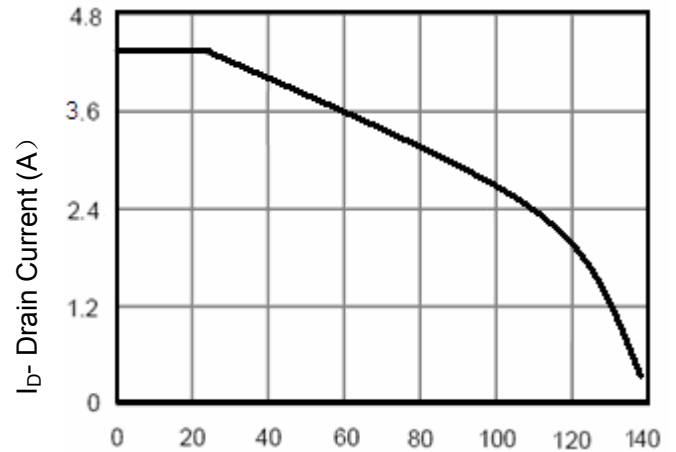


Figure 4 Drain Current

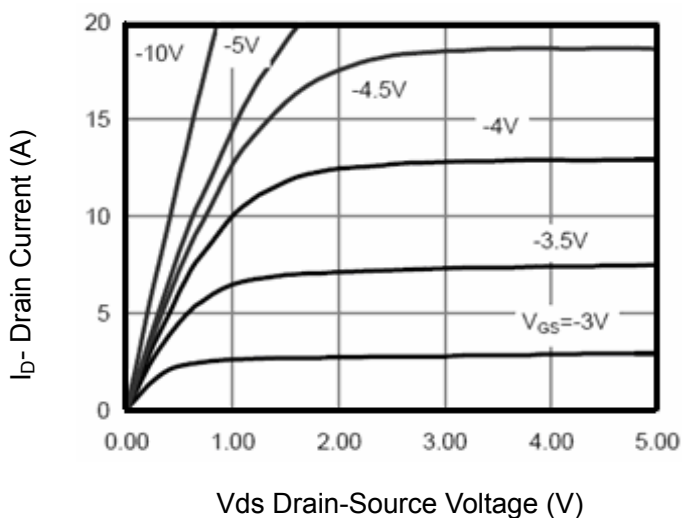


Figure 5 Output CHARACTERISTICS

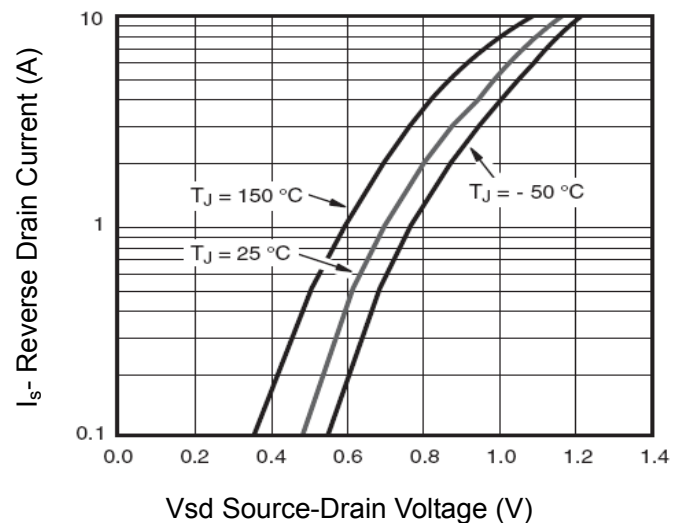


Figure 6 Source- Drain Diode Forward

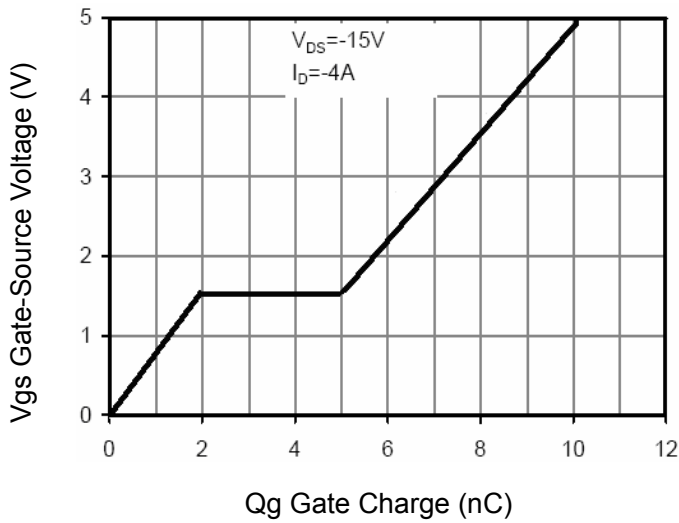


Figure 7 Gate Charge

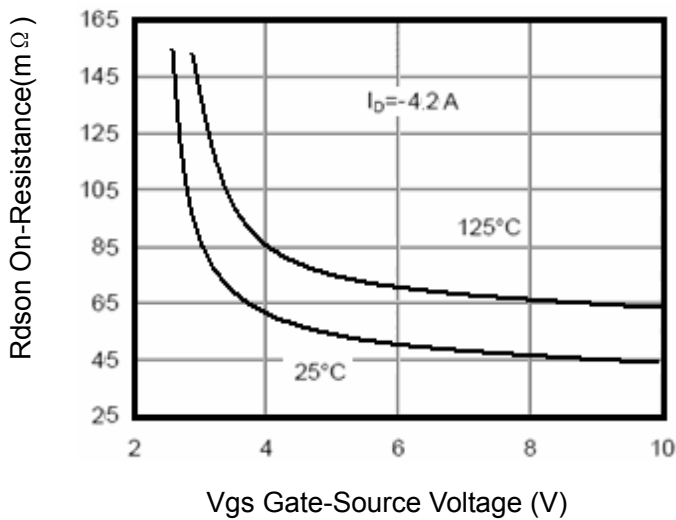


Figure 9 Rdson vs Vgs

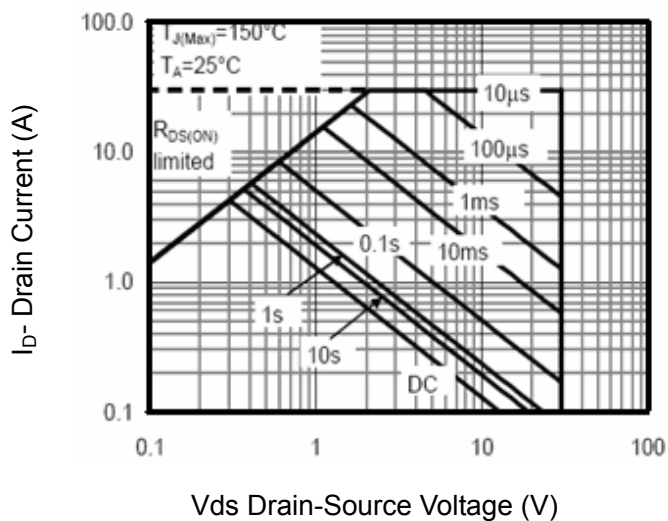


Figure 11 Safe Operation Area

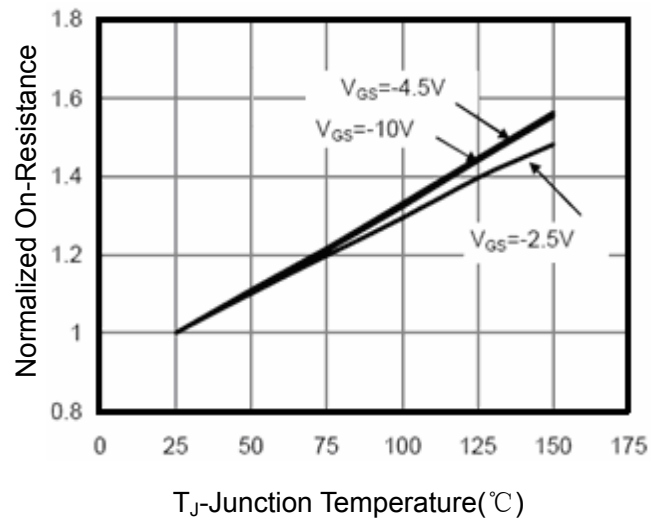


Figure 8 Drain-Source On-Resistance

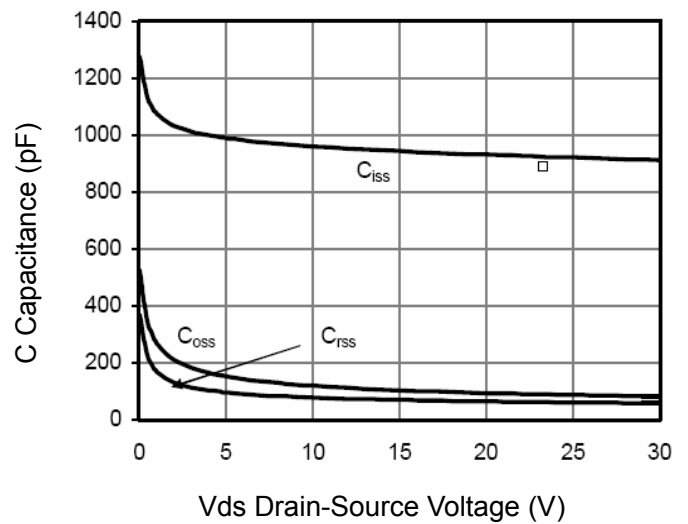


Figure 10 Capacitance vs Vds

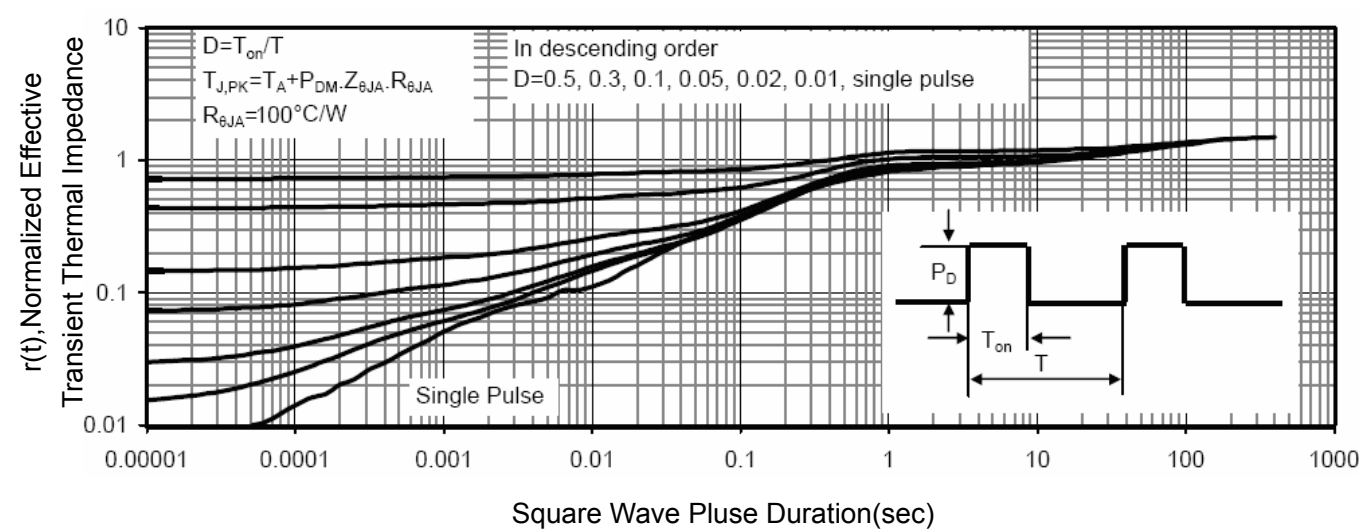
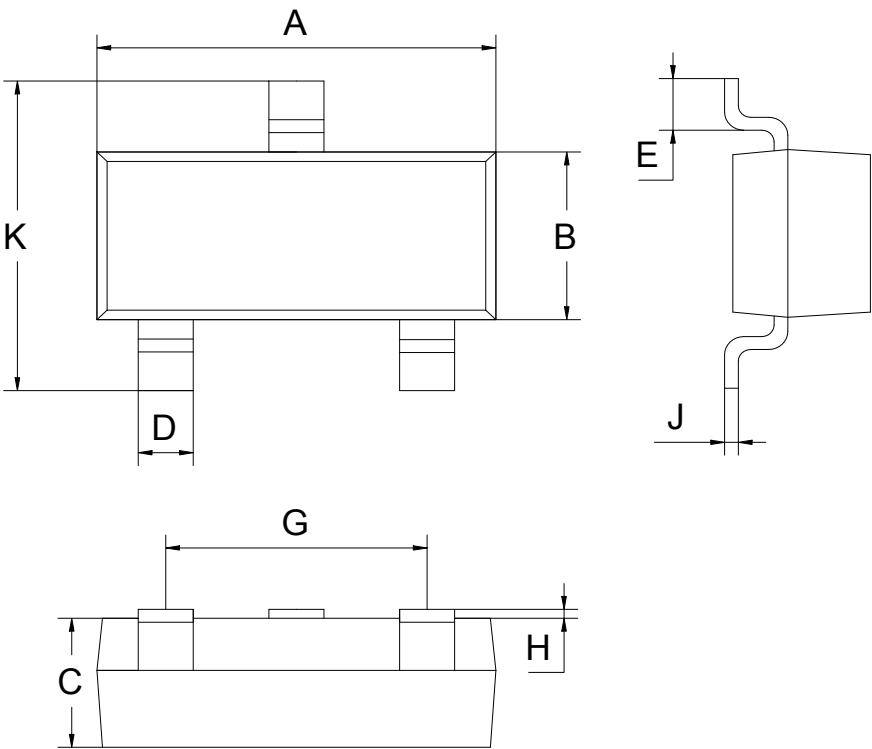


Figure 12 Normalized Maximum Transient Thermal Impedance

SOT-23 Package information



SOT-23			
Dim	MIN	NOM	MAX
A	2.80	2.90	3.00
B	1.20	1.30	1.40
C	0.90	1.00	1.10
D	0.39	0.40	0.45
E	0.20MIN		
G	1.90REF		
H	0.00	-	0.10
J	0.05	0.10	0.15
K	2.30	2.40	2.50
All Dimensions in mm			